

SURFACE MOUNT SCHOTTKY BARRIER DIODE ARRAY

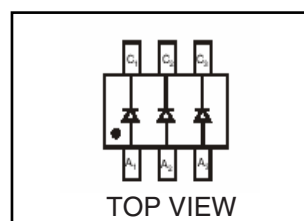
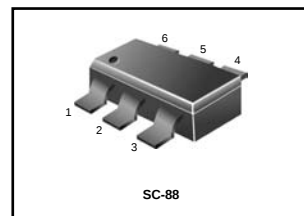
These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

- Extremely Fast Switching Speed
- Low Forward Voltage — 0.35 Volts (Typ) @ $I_F = 10 \text{ mAdc}$
- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBAT54TW1T1G S-LBAT54TW1T1G	KLA	3000/Tape&Reel
LBAT54TW1T3G S-LBAT54TW1T3G	KLA	10000/Tape&Reel

LBAT54TW1T1G S-LBAT54TW1T1G



MAXIMUM RATINGS ($T_J = 125^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	30	Volts
Forward Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 2.0	mW mW/ $^\circ\text{C}$
Forward Current (DC)	I_F	200 Max	mA
Junction Temperature	T_J	125 Max	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage ($I_R = 10 \mu\text{A}$)	$V_{(BR)R}$	30	—	—	Volts
Total Capacitance ($V_R = 1.0 \text{ V}$, $f = 1.0 \text{ MHz}$)	C_T	—	—	10	pF
Reverse Leakage ($V_R = 25 \text{ V}$)	I_R	—	0.5	2.0	μAdc
Forward Voltage ($I_F = 0.1 \text{ mAdc}$)	V_F	—	0.22	0.24	Vdc
Forward Voltage ($I_F = 30 \text{ mAdc}$)	V_F	—	0.41	0.5	Vdc
Forward Voltage ($I_F = 100 \text{ mAdc}$)	V_F	—	0.52	1.0	Vdc
Reverse Recovery Time ($I_F = I_R = 10 \text{ mAdc}$, $I_{R(REC)} = 1.0 \text{ mAdc}$) Figure 1	t_{rr}	—	—	5.0	ns
Forward Voltage ($I_F = 1.0 \text{ mAdc}$)	V_F	—	0.29	0.32	Vdc
Forward Voltage ($I_F = 10 \text{ mAdc}$)	V_F	—	0.35	0.40	Vdc
Forward Current (DC)	I_F	—	—	200	mAdc
Repetitive Peak Forward Current	I_{FRM}	—	—	300	mAdc
Non-Repetitive Peak Forward Current ($t < 1.0 \text{ s}$)	I_{FSM}	—	—	600	mAdc

LBAT54TW1T1G , S-LBAT54TW1T1G

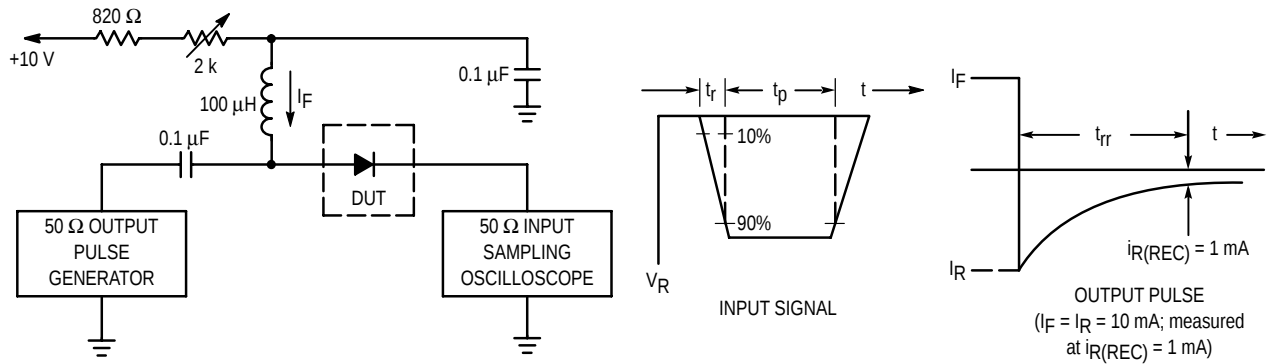


Figure 1. Recovery Time Equivalent Test Circuit

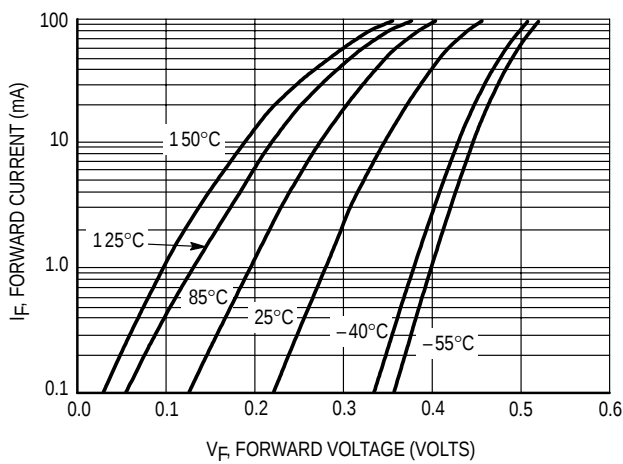


Figure 2. Forward Voltage

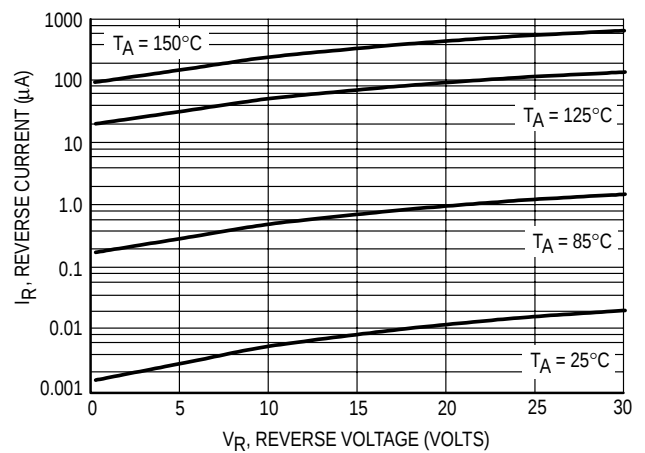


Figure 3. Leakage Current

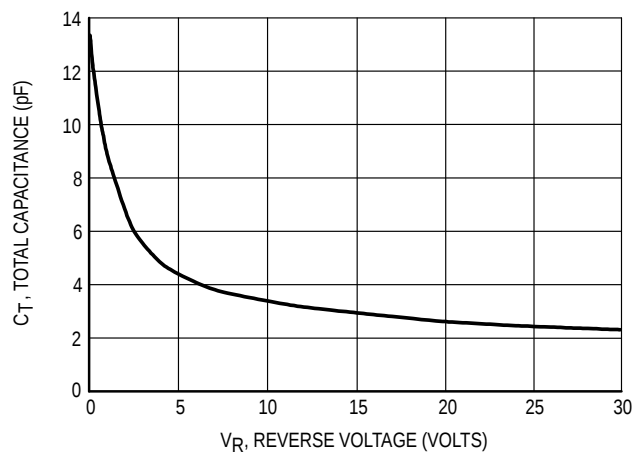


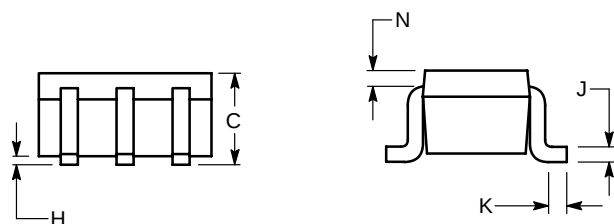
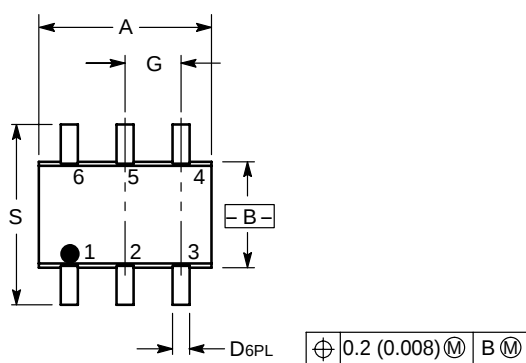
Figure 4. Total Capacitance

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NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

- PIN 1. EMITTER 2
 2. BASE 2
 3. COLLECTOR 1
 4. EMITTER 1
 5. BASE 1
 6. COLLECTOR 2

